

Abstract

1. A semiconductor device fabrication process comprising the steps of: (a) forming a dummy gate pattern on a semiconductor substrate with the intervention of a gate insulating film; (b) forming a sidewall insulating film on a side wall of the dummy gate pattern; (c) forming a film of the same material as a material for the dummy gate pattern at least in a contact plug formation region on the semiconductor substrate; (d) forming an interlayer insulating film around the same material film on the semiconductor substrate; (e) removing the dummy gate pattern and the same material film located in the contact plug formation region to form trenches in the interlayer insulating film; and (f) filling the trenches with an electrically conductive material to form a gate electrode and a contact plug.